

自主封測 品質把控 售後保障

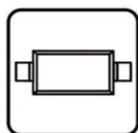
WEB | WWW.TDSEMIC.COM



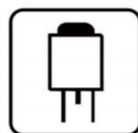
電源管理



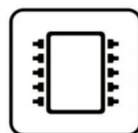
顯示驅動



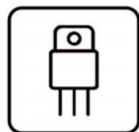
二三極管



LDO穩壓器



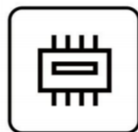
觸摸芯片



MOS管



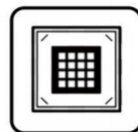
運算放大器



存儲芯片



MCU



串口通信

TD4882

產品規格說明書

Description

The TD4882 is the high cell density trenched N-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The TD4882 meet the RoHS and Green Product

- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

Application

Battery protection

Load switch

Uninterruptible power supply

General Features

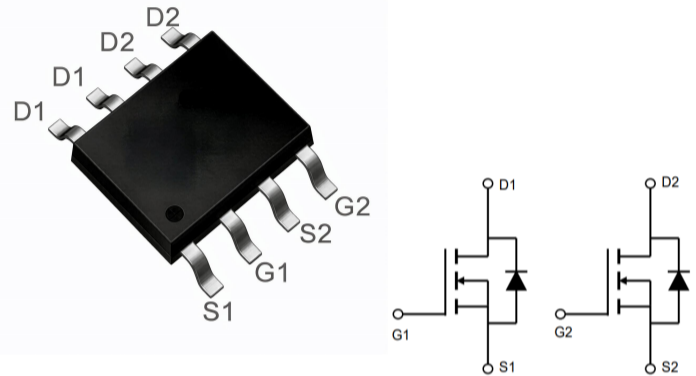
$V_{DS} = 40V$ $I_D = 10A$

$R_{DS(ON)} < 22m\Omega$ @ $V_{GS}=10V$

$R_{DS(ON)} < 35m\Omega$ @ $V_{GS}=4.5V$



SOP-8 Pin Configuration



Package Marking and Ordering Information

Product ID	Package	Marking	QTY(PCS)	Packing method
TD4882	SOP-8	4882	3000	Reel

Absolute Maximum Ratings (TA=25°C unless otherwise specified)

Symbol	Parameter		Max.	Units
V_{DSS}	Drain-Source Voltage		40	V
V_{GSS}	Gate-Source Voltage		± 20	V
I_D	Continuous Drain Current	$T_A = 25^\circ C$	10	A
		$T_A = 100^\circ C$	7	A
I_{DM}	Pulsed Drain Current ^{note1}		32.8	A
EAS	Single Pulsed Avalanche Energy ^{note2}		13	mJ
P_D	Power Dissipation	$T_A = 25^\circ C$	2.9	W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient		63	$^\circ C/W$
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	$^\circ C$

N-Channel Electrical Characteristics (T_J=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	40	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =40V, V _{GS} =0V	-	-	1.0	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} =±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.0	1.5	2.5	V
R _{DS(on)}	Static Drain-Source on-Resistance note3	V _{GS} =10V, I _D =8A	-	17	22	mΩ
		V _{GS} =4.5V, I _D =5A	-	25	35	mΩ
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =20V, V _{GS} =0V, f=1.0MHz	-	633	-	pF
C _{oss}	Output Capacitance		-	67	-	pF
C _{rss}	Reverse Transfer Capacitance		-	58	-	pF
Q _g	Total Gate Charge	V _{DS} =20V, I _D =8A, V _{GS} =10V	-	12	-	nC
Q _{gs}	Gate-Source Charge		-	3.2	-	nC
Q _{gd}	Gate-Drain(“Miller”) Charge		-	3.1	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DD} = 20V, R _L =2.5Ω V _{GS} =10V,R _{REN} =3Ω	-	4	-	ns
t _r	Turn-on Rise Time		-	3	-	ns
t _{d(off)}	Turn-off Delay Time		-	15	-	ns
t _f	Turn-off Fall Time		-	2	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	8	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	32	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _S = 8A	-	-	1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition : T_J=25°C, V_{DD}=20V, V_G=10V, L=0.5mH, R_g=25Ω, I_{AS}=7.2A

T_J=25°C, V_{DD}=-20V, V_G= -10V, L=0.5mH, R_g=25Ω, I_{AS}=-8.4A

3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%

Typical Performance Characteristics-N

Figure 1: Output Characteristics

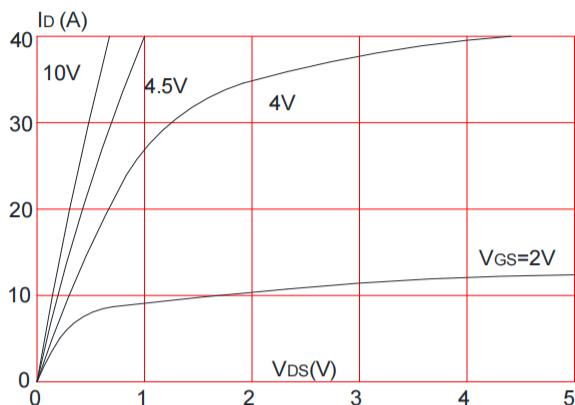


Figure 2: Typical Transfer Characteristics

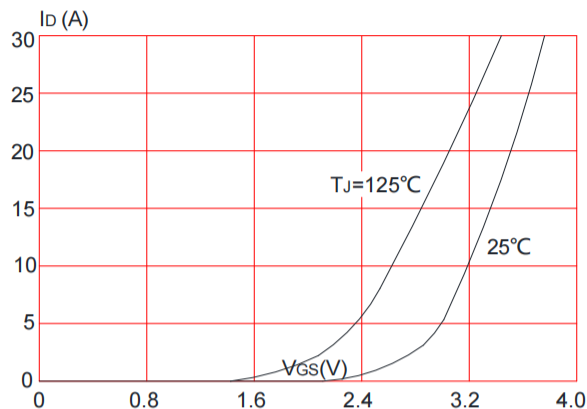


Figure 3: On-resistance vs. Drain Current

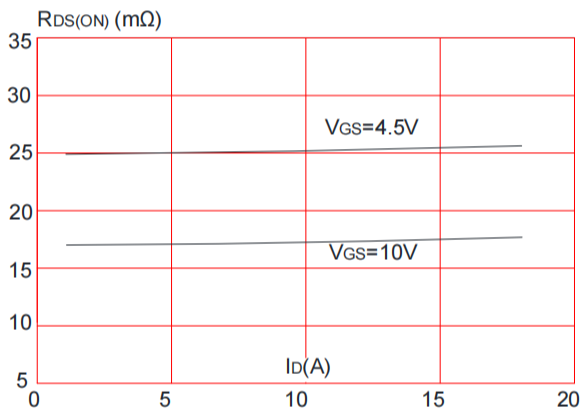


Figure 4: Body Diode Characteristics

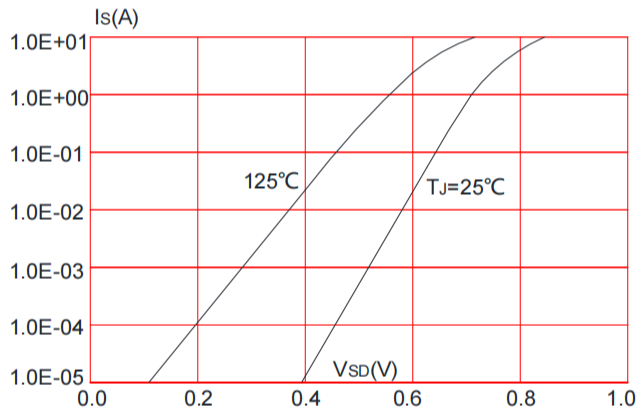


Figure 5: Gate Charge Characteristics

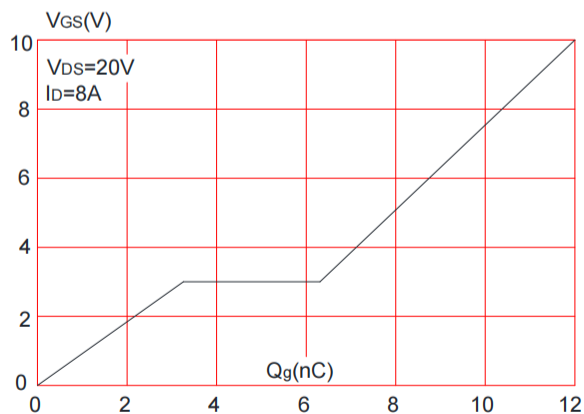


Figure 6: Capacitance Characteristics

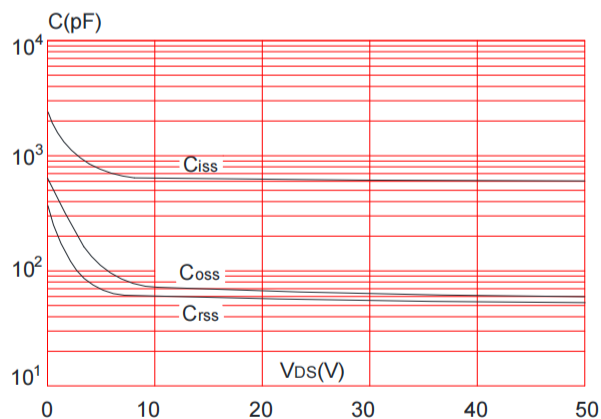


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

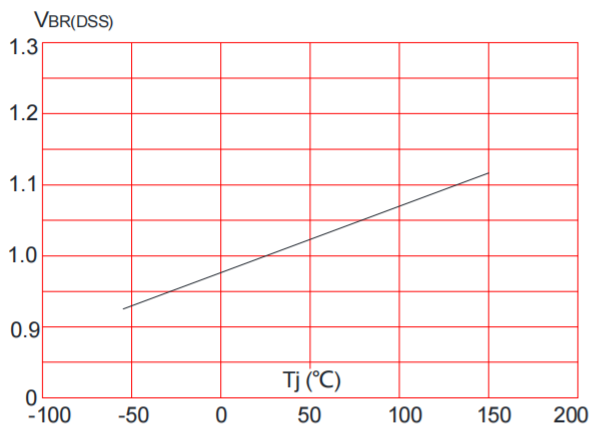


Figure 8: Normalized on Resistance vs. Junction Temperature

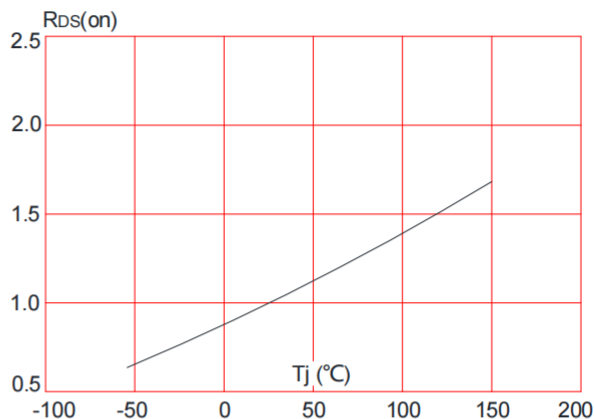


Figure 9: Maximum Safe Operating Area

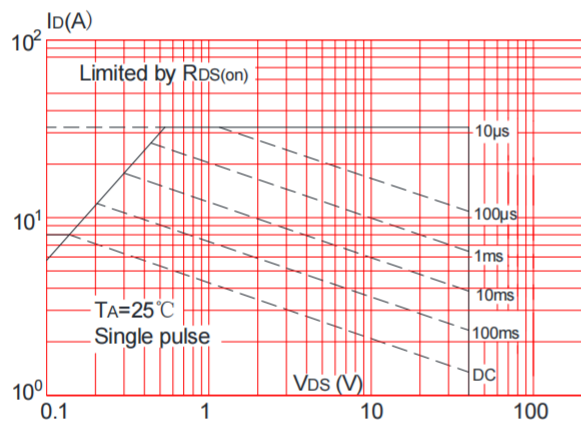


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

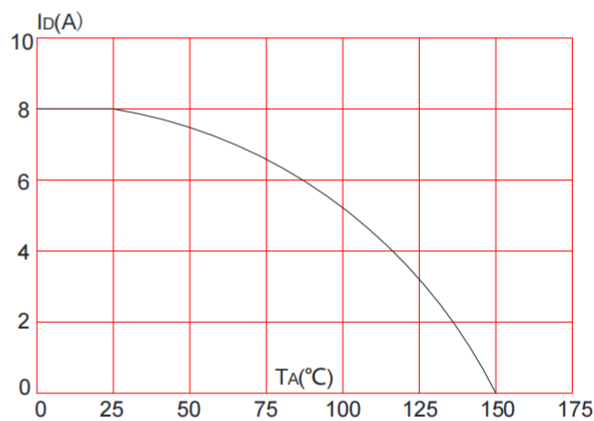
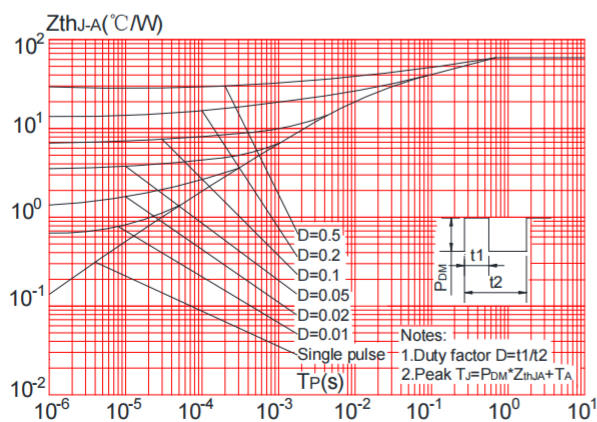
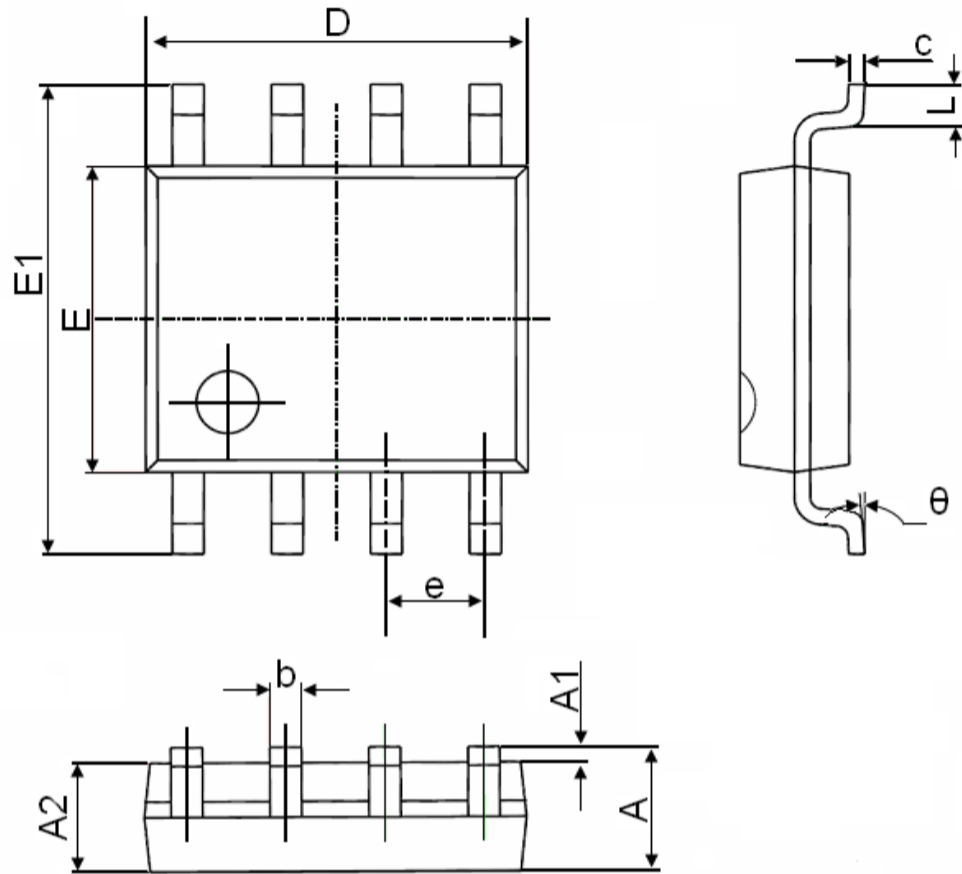


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



SOP-8 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°